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# 2SC3553

Silicon NPN Epitaxial

# HITACHI

ADE-208-1090 (Z)  
1st. Edition  
Mar. 2001

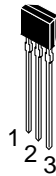
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## Application

Low frequency amplifier

## Outline

SPAK



1. Emitter
2. Collector
3. Base

## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	35	V
Collector to emitter voltage	$V_{CEO}$	35	V
Emitter to base voltage	$V_{EBO}$	4	V
Collector current	$I_C$	500	mA
Collector power dissipation	$P_C$	300	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

## Electrical Characteristics (Ta = 25°C)

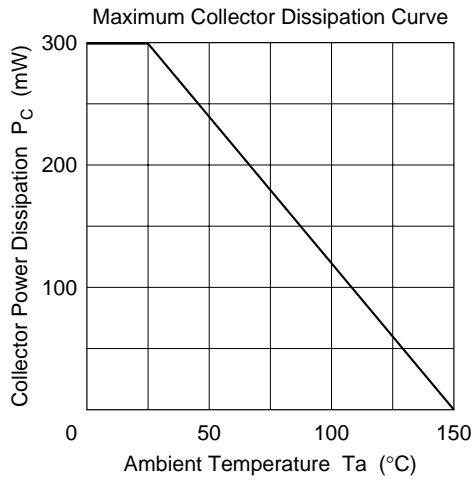
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	35	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	35	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CB} = 20 \text{ V}, I_E = 0$
DC current transfer ratio	$h_{FE1}^{*1}$	60	—	320		$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$
	$h_{FE2}$	10	—	—		$V_{CE} = 3 \text{ V}, I_C = 500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.2	0.6	V	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^{*2}$
Base to emitter voltage	$V_{BE}$	—	0.64	—	V	$V_{CE} = 3 \text{ V}, I_C = 10 \text{ mA}$

Notes: 1. The 2SC3553 is grouped by  $h_{FE1}$  as follows.

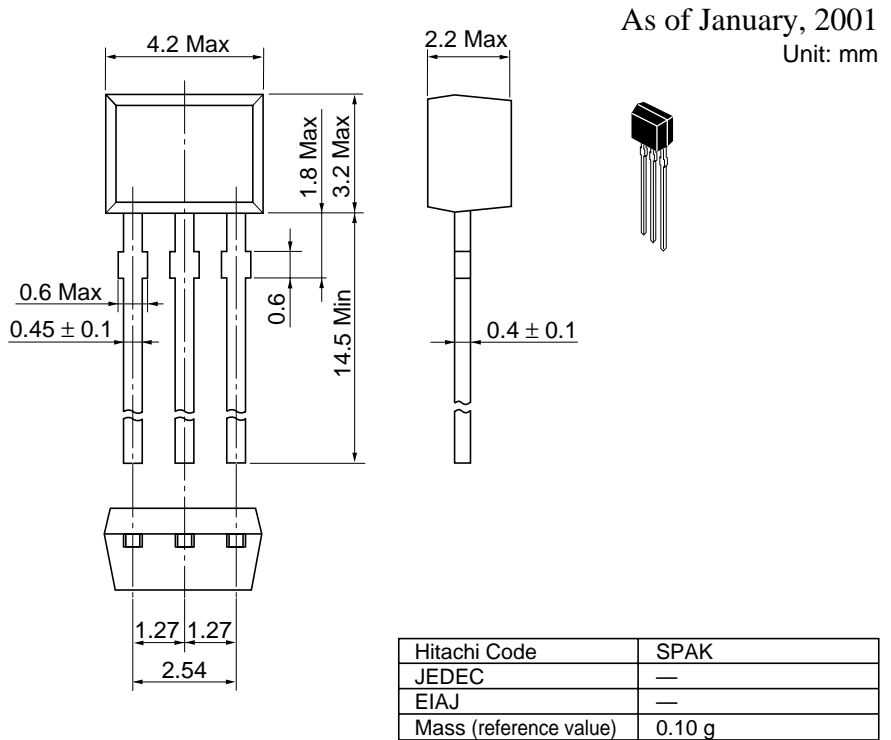
2. Pulse test

B	C	D
60 to 120	100 to 200	160 to 320

See characteristic curves of 2SC1213.



## Package Dimensions



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# HITACHI

## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: <a href="http://semiconductor.hitachi.com/">http://semiconductor.hitachi.com/</a>
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### For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic Components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 585160

Hitachi Asia Ltd.  
Hitachi Tower  
16 Collyer Quay #20-00,  
Singapore 049318  
Tel: <65>-538-6533/538-8577  
Fax: <65>-538-6933/538-3877  
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.  
(Taipei Branch Office)  
4/F, No. 167, Tun Hwa North Road,  
Hung-Kuo Building,  
Taipei (105), Taiwan  
Tel: <886>-(2)-2718-3666  
Fax: <886>-(2)-2718-8180  
Telex: 23222 HAS-TP  
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower,  
World Finance Centre,  
Harbour City, Canton Road  
Tsim Sha Tsui, Kowloon,  
Hong Kong  
Tel: <852>-(2)-735-9218  
Fax: <852>-(2)-730-0281  
URL: <http://www.hitachi.com.hk>

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